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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Ji Ung Lee et al.		GROUP Filed Herewith	
					FILING DATE Filed Herewith			
U.S. PATENT DOCUMENTS								
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate		
STF	AA	5,482,870	Inoue					
STF	AB	5,372,973	Doan et al.					
STF	AC	5,229,331	Doan et al.					
STF	AD	5,210,472	Casper et al.					
STF	AE	4,988,638	Huang et al.					
STF	AF	6,057,555	Reedy et al.					
STF	AG	5,710,478	Kanemaru et al.					
STF	AH	6,020,683	Cathey, Jr. et al.					
STF	AI	6,249,327 B1	Murade et al.					
	AJ							
	AK							
FOREIGN PATENT DOCUMENTS								
	Document Number	Date	Country	Class	Subclass	Translation		
						Yes	No	
STF	AL	5-114734	Japan			X		
STF	AM	3-194937	Japan			X		
STF	AN	3-159250	Japan			X		
STF	AO	A-2-143482	Japan			X		
STF	AP	61-252687	Japan			X		
STF	AQ	A-57-85282	Japan			X		
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
STF	AR		Polycrystalline Silicon Thin Film Transistor Incorporating a Semi-Insulating Field Plate for High Voltage Circuitry on Glass.					
			F.J. Clough, E.M.S. Narayanan, Y. Chen, W. Eccleston, and W.I. Milne, Appl. Phys. Lett. 71 - 10/06/97, pages 2002-2004, 1997 American Institute of Physics.					
STF	AS		Geometry Dependence of the Transport Parameters in Field Effect Transistors Made From Amorphous Silicon, S. Glep, Mat. Res. Soc. Symp. Proc. 148,					
			pages 283-288, 1989 Materials Research Society.					
	AT							
EXAMINER <i>Steve Gull</i>				DATE CONSIDERED <i>1/26/06</i>				
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